REMARKS

In the above-identified Office Action, the Examiner has objected to claims 5, 6, 10, 11 and 17 to 22 because the Examiner states that the measurement of the dots does not specify the dimension. The Applicant has inserted the word "wide" into each of the objected to claims, indicating the dimension in which the dot is to be measured. Support for this is found inherently in the application as a whole, as well as page 13, line 4, indicating that the marks have a width.

In addition, the Examiner has rejected claims 1 through 25 as being unpatentable over the combination of Huang et al. in view of Yano et al. The Examiner has stated in view of the teaching of Yano would have been obvious to one of ordinary skill to employ the mark at a spaced apart location to ensure at least one of the marks was still available to read. However, neither Huang nor Yano teach the use of a substantially duplicate mark in conjunction with the original mark. Yano is concerned with using a combination of bar codes and visible numerals and alphabets on a side surface portion of the semiconductor wafer which will not be obliterated in the manufacturing process. However, Yano does not teach the use of at least two substantially-identical marks on the same semiconductor wafer. However, the Examiner has admitted that Huang fails to teach that the new mark is formed in another location spaced apart from the substantially effaced mark. Accordingly, the references cited do not teach the subject application as claimed.

Applicant hereby requests reconsideration and reexamination thereof.

With the above amendments and remarks, this application is considered ready for allowance and Applicant earnestly solicits an early notice of same. Should the Examiner be of the opinion that a telephone conference would expedite prosecution of the subject application, he is respectfully requested to call the undersigned at the below-listed number.

Respectfully submitted,

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By 

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

5. (Amended) The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is formed by means of a combination of dots, each dot measuring 1 to 13 μm wide, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity fo the substantially-effaced mark.

6. (Amended) The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is a minute ID mark which is assigned to the semiconductor wafer and is formed by means of a combination of dots, each dot measuring 1 to 13 μm wide, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

10. (Amended) The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is formed by means of a combination of dots, each dot measuring μm wide, and is affixed on the interior wall surface of a notch, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

11. (Amended) The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is an ID mark which is assigned to the semiconductor wafer, is formed by means of a combination of dots, each dot measuring μm wide, and is affixed on the interior wall surface of a notch, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

17. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring μm wide, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of

manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

18. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are minute ID marks which are assigned to the semiconductor wafer and are formed by means of a combination of dots, each dot measuring μm wide, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

19. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are minute ID marks which are assigned to the semiconductor wafer, are formed by means of a combination of dots, each dot measuring 1 to 13 μm wide, and are affixed on the interior wall surface of a notch, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

20. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring 1 to 13 μm wide, for positioning purpose, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

21. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring μm wide and indicate crystal orientation of the semiconductor wafer, and some of two or more

essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

22. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein the semiconductor wafer is perfectly annular; two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring μm wide, at least one of the two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.